



LET9002

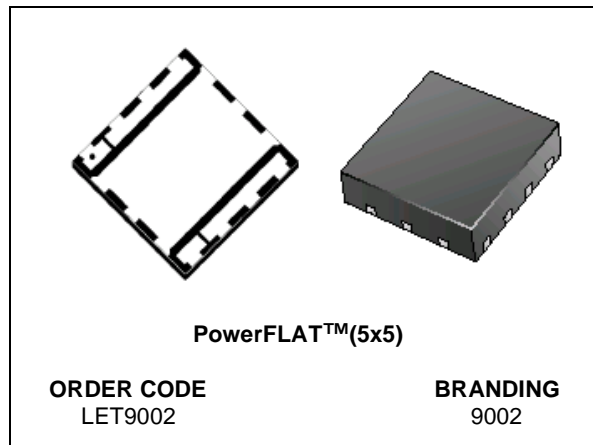
RF POWER TRANSISTORS

Ldmos Enhanced Technology in Plastic Package

TARGET DATA

N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

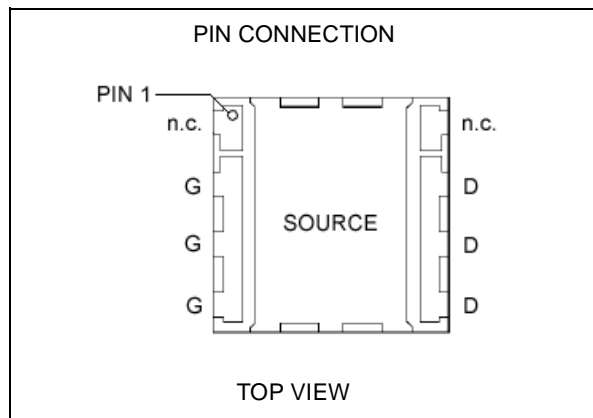
- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{OUT} = 2\text{ W}$ with 17 dB gain @ 960 MHz / 26 V
- NEW LEADLESS PLASTIC PACKAGE
- ESD PROTECTION
- SUPPLIED IN TAPE & REEL OF 3K UNITS



DESCRIPTION

The LET9002 is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1000 MHz. The LET9002 is designed for high gain and broadband performance operating in common source mode at 26 V. LET9002 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the innovative leadless SMD plastic package, PowerFLAT™.

It is ideal for digital cellular BTS applications requiring high linearity.



ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25 °C)

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-Source Voltage	65	V
V _{GS}	Gate-Source Voltage	-0.5 to +15	V
I _D	Drain Current	0.25	A
P _{DISS}	Power Dissipation (@ T _c = 70°C)	4	W
T _j	Max. Operating Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{th(j-c)}	Junction -Case Thermal Resistance	20	°C/W
----------------------	-----------------------------------	----	------

ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

STATIC

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V	I _{DS} = 1 mA	65			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 26 V			1	μA
I _{GSS}	V _{GS} = 5 V	V _{DS} = 0 V			1	μA
V _{GS(Q)}	V _{DS} = 26 V	I _D = TBD	2.0		5.0	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 125 mA			0.9	V
g _{FS}	V _{DS} = 10 V	I _D = 200 mA		--		mho
C _{ISS}	V _{GS} = 0 V	V _{DS} = 26 V		f = 1 MHz	TBD	pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 26 V		f = 1 MHz	TBD	pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 26 V		f = 1 MHz	TBD	pF

DYNAMIC (f = 960 MHz)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
P _{out} ⁽¹⁾	V _{DD} = 26 V	I _{DQ} = TBD	2.5	3		W
η _D ⁽¹⁾	V _{DD} = 26 V	I _{DQ} = TBD P _{OUT} = 2 W	55	65		%
Load mismatch	V _{DD} = 26 V	I _{DQ} = TBD P _{OUT} = 2 W ALL PHASE ANGLES			10:1	VSWR

(1) 1 dB Compression point

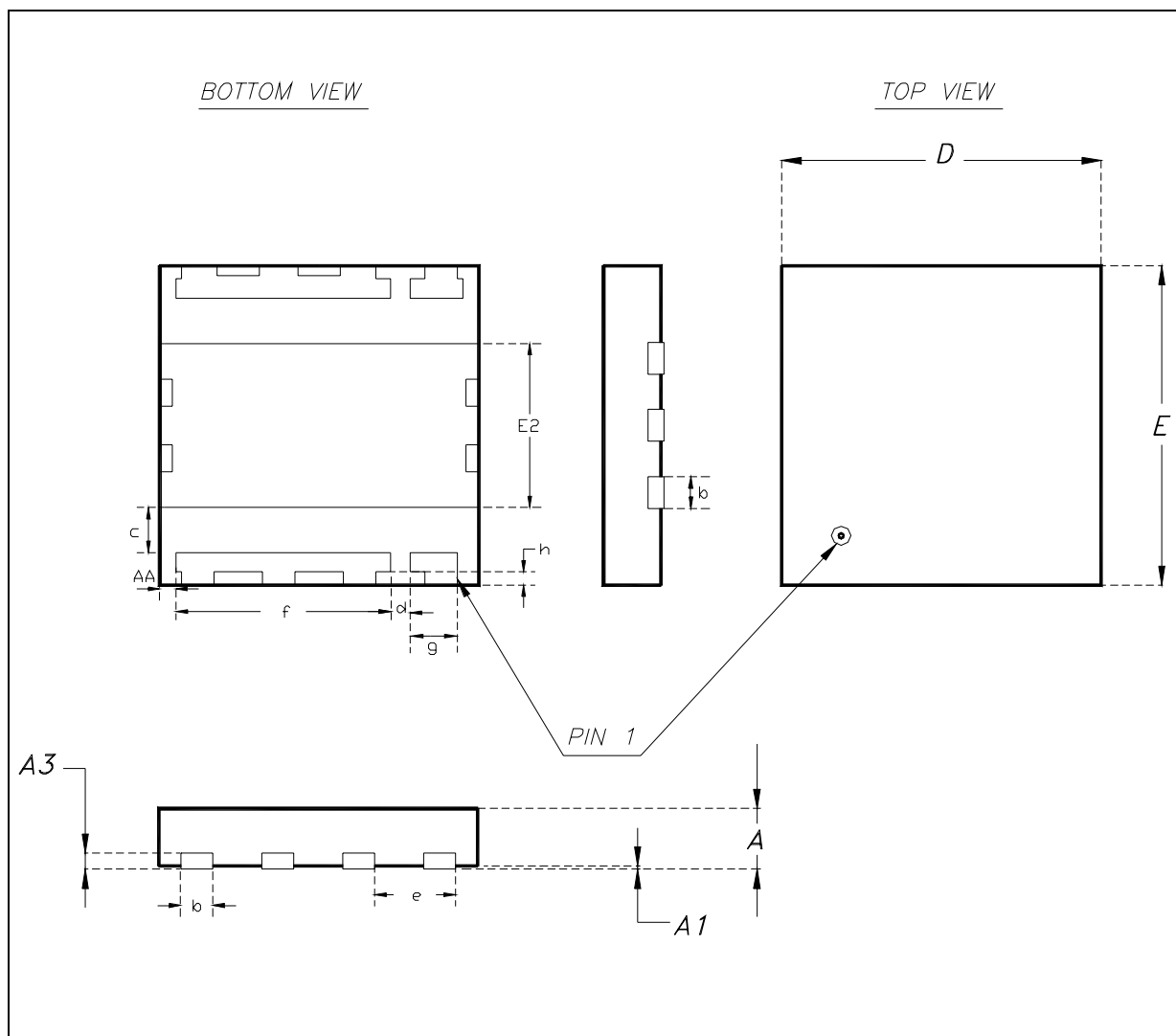
DYNAMIC (f = 920 - 960 MHz)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
P _{out} ⁽¹⁾	V _{DD} = 26 V	I _{DQ} = TBD	2	2.5		W
η _D ⁽¹⁾	V _{DD} = 26 V	I _{DQ} = TBD	55	60		%
G _P	V _{DD} = 26 V	I _{DQ} = TBD P _{OUT} = 2 W	17			dB

(1) 1 dB Compression point

PowerFLAT™ MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A		0.90	1.00		0.035	0.039
A1		0.02	0.05		0.001	0.002
A3		0.24			0.009	
AA	0.15	0.25	0.35	0.006	0.01	0.014
b	0.43	0.51	0.58	0.017	0.020	0.023
c	0.64	0.71	0.79	0.025	0.028	0.031
D		5.00			0.197	
d		0.30			0.011	
E		5.00			0.197	
E2	2.49	2.57	2.64	0.098	0.101	0.104
e		1.27			0.050	
f		3.37			0.132	
g		0.74			0.03	
h		0.21			0.008	



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics
© 2003 STMicroelectronics - All Rights Reserved

All other names are the property of their respective owners.

STMicroelectronics GROUP OF COMPANIES
Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.
<http://www.st.com>